L Number	Hits	Search Text	DB	Time stamp
1	3	"2002093705"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/01 15:17
2	1383	(silicon or si) same (ge or germanium) same laminat$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/01 15:18
3	449	(silicon or si) same (ge or germanium) same laminat$4 same amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/01 15:18
4	0	(silicon or si) same (ge or germanium) same laminat$4 same amorphous and 117/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/01 15:18
5	0	(silicon or si) same (ge or germanium) same laminat$4 same amorphous and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/01 15:18
6	85	(silicon or si) same (ge or germanium) same laminat$4 same amorphous and 257/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/01 15:20
7	33	(silicon or si) same (ge or germanium) same laminat$4 same amorphous and laser near10 (crystalliz$4 or crystal$4 or anneal$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/01 15:25
8	78	(silicon or si) same (ge or germanium) same laminat$4 same amorphous same (crystalliz$4 or crystal$4 or anneal$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/01 15:26
9	12	(silicon or si) same (ge or germanium) same laminat$4 same amorphous same (crystalliz$4 or anneal$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/01 15:26

L Number	Hits	Search Text	DB	Time stamp
-	93	yamazaki.in. and (ge or germanium) same laser same anneal$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/31 16:17
-	118	(ge or germanium) near10 amorphous same (si or silicon) near10 amorphous same anneal$4 same (crystal$4 or crystalliz$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/31 16:23
-	4	(ge or germanium) near10 amorphous same (si or silicon) near10 amorphous same anneal$4 same (crystal$4 or crystalliz$4) same (first and second)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/31 16:36
-	21	(ge or germanium) near10 amorphous near5 (first or second) same laser and (si or silicon) near10 amorphous near10 (first or second)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/31 16:54
-	9	(ge or germanium) near10 amorphous near5 (first or second) same anneal$4 and (si or silicon) near10 amorphous near10 (first or second)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/31 16:58
-	172	(shunpei.in. near2 yamazaki.in.) and laser near3 (crystal$4 or crystalliz$4 or anneal$4) same (silicon or si) and (ge or germanium) near10 amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/01 10:47
-	14	(shunpei.in. near2 yamazaki.in.) and laser near3 (crystal$4 or crystalliz$4 or anneal$4) and first near10 (ge or germanium) near10 amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/01 10:50
-	49	(shunpei.in. near2 yamazaki.in.) and laser near3 (crystal$4 or crystalliz$4 or anneal$4) and (ge or germanium) near10 amorphous and second near10 (film or layer) near10 amorphous near10 (si or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/01 11:20
-	97	(shunpei.in. near2 yamazaki.in.) and laser near3 (crystal$4 or crystalliz$4 or anneal$4) same ((silicon or si) and (ge or germanium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/01 11:21
-	85	(shunpei.in. near2 yamazaki.in.) and laser near3 (crystal$4 or crystalliz$4 or anneal$4) same ((silicon or si) and (ge or germanium)) same amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/01 11:22
-	18	(semiconductor near2 energy near2 laboratory or sel).as. and laser near3 (crystal$4 or crystalliz$4 or anneal$4) and ((silicon or si) and (ge or germanium)) same amorphous same first same second	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/01 11:29